IEEE Xplore RELEASE 2.1

Home | Login | Logout | Access Information | Alerts |

Welcome United States Patent and Trademark Office

Search Results BROWSE SEARCH IEEE XPLORE GUIDE

Results for "(((electromigration <and> plugs)<in>metadata)) <and> (pyr >= 1951 <and> p..." e-mail
Your search matched **12** of **1243738** documents.
A maximum of **100** results are displayed, **25** to a page, sorted by **Relevance** in **Descending** order.

» Search Options

View Session History

New Search

Modify Search

(((electromigration <and> plugs)<in>metadata)) <and> (pyr >= 1951 <and> pyr <= 19 >>

Check to search only within this results set

Display Format: (•) Citation ( ) Citation & Abstract

» Key

IEEE JNL	IEEE Journal or Magazine
IEE JNL	IEE Journal or Magazine
IEEE CNF	IEEE Conference Proceeding
IEE CNF	IEE Conference Proceeding
IEEE STD	IEEE Standard

Select **Article Information**

1. **A novel 0.25 µm via plug process using low temperature CVD Al/TiN**
Dixit, G.A.; Paranjpe, A.; Qi-Zhong Hong; Ting, L.M.; Luttmer, J.D.; Havemann
Morrison, A.; Littau, K.; Eizenberg, M.; Sinha, A.K.;
Electron Devices Meeting, 1995., International
10-13 Dec. 1995 Page(s):1001 - 1004
Digital Object Identifier 10.1109/IEDM.1995.499385
AbstractPlus | Full Text: PDF(328 KB) **IEEE CNF**

2. **A 0.25 µm via plug process using selective CVD aluminium for multilevel**
Amazawa, T.; Arita, Y.;
Electron Devices Meeting, 1991. Technical Digest., International
8-11 Dec. 1991 Page(s):265 - 268
Digital Object Identifier 10.1109/IEDM.1991.235452
AbstractPlus | Full Text: PDF(256 KB) **IEEE CNF**

3. **Electromigration characteristics of tungsten plug vias under pulse and bi current stressing**
Tao, J.; Young, K.K.; Pico, C.A.; Cheung, N.W.; Hu, C.;
Electron Device Letters, IEEE
Volume 12, Issue 12, Dec. 1991 Page(s):646 - 648
Digital Object Identifier 10.1109/55.116942
AbstractPlus | Full Text: PDF(228 KB) **IEEE JNL**

4. **Electromigration reliability of tungsten and aluminum vias and improvem current stress**
Tao, J.; Young, K.K.; Cheung, N.W.; Hu, C.;
Electron Devices, IEEE Transactions on
Volume 40, Issue 8, Aug. 1993 Page(s):1398 - 1405
Digital Object Identifier 10.1109/16.223698
AbstractPlus | Full Text: PDF(764 KB) **IEEE JNL**

5. **Electromigration characteristics of Al/W via contact under unidirectional current conditions**
Jiang Tao; Young, K.K.; Pico, C.A.; Cheung, N.W.; Chenming Hu;
VLSI Multilevel Interconnection Conference, 1991, Proceedings., Eighth Intern
11-12 June 1991 Page(s):390 - 392
Digital Object Identifier 10.1109/VMIC.1991.153034
AbstractPlus | Full Text: PDF(228 KB) **IEEE CNF**

6. **Comparison of electromigration reliability of tungsten and aluminum vias time-varying current stressing**
Tao, J.; Young, K.K.; Cheung, N.W.; Hu, C.;
Reliability Physics Symposium 1992. 30th Annual Proceedings., International
31 March-2 April 1992 Page(s):338 - 343
Digital Object Identifier 10.1109/RELPHY.1992.187667
AbstractPlus | Full Text: PDF(440 KB) **IEEE CNF**

7. **Fully planarized four-level interconnection with stacked vias using CMP c Al and insulator and its application to quarter micron gate array LSIs**
Amazawa, T.; Yamamoto, E.; Sakuma, K.; Ito, Y.; Kamoshida, K.; Ikeda, K.; Sa Kato, S.; Yagi, S.; Hiraoka, K.; Ueki, T.; Takeda, T.; Arita, Y.;
Electron Devices Meeting, 1995., International
10-13 Dec. 1995 Page(s):473 - 476
Digital Object Identifier 10.1109/IEDM.1995.499241
AbstractPlus | Full Text: PDF(664 KB) **IEEE CNF**

8. **Electromigration reliability improvement of W-plug vias by titanium layeri**
Graas, C.D.; Le, H.A.; McPherson, J.W.; Havemann, R.H.;
Reliability Physics Symposium, 1994. 32nd Annual Proceedings., IEEE Interna
11-14 April 1994 Page(s):173 - 177
Digital Object Identifier 10.1109/RELPHY.1994.307840
AbstractPlus | Full Text: PDF(600 KB) **IEEE CNF**

9. **Reliability study of planarized aluminum metallization**
Hoang, H.H.; Chen, F.S.; Zamanian, M.; Dixit, G.A.; Wei, C.C.; Liou, F.T.;
VLSI Multilevel Interconnection Conference, 1991, Proceedings., Eighth Intern
11-12 June 1991 Page(s):411 - 413
Digital Object Identifier 10.1109/VMIC.1991.153041
AbstractPlus | Full Text: PDF(284 KB) **IEEE CNF**

10. **Stress-voiding in tungsten-plug interconnect systems induced by high-te processing**
Walls, J.A.;
Electron Device Letters, IEEE
Volume 16, Issue 10, Oct. 1995 Page(s):430 - 432
Digital Object Identifier 10.1109/55.464807
AbstractPlus | Full Text: PDF(228 KB) **IEEE JNL**

11. **A highly reliable multilevel interconnection process for 0.6 μm CMOS dev**
Takata, Y.; Ishii, A.; Matsuura, M.; Ohsaki, A.; Iwasaki, M.; Miyazaki, J.; Fujiwa Katayama, T.; Nakao, S.; Kotani, H.;
VLSI Multilevel Interconnection Conference, 1991, Proceedings., Eighth Intern
11-12 June 1991 Page(s):13 - 19
Digital Object Identifier 10.1109/VMIC.1991.152960
AbstractPlus | Full Text: PDF(436 KB) **IEEE CNF**

12. **Enhanced selective tungsten encapsulation of TiW capped aluminum int**
Dalton, C.M.;
VLSI Multilevel Interconnection Conference, 1990. Proceedings., Seventh Inte
12-13 June 1990 Page(s):289 - 295
Digital Object Identifier 10.1109/VMIC.1990.127879
AbstractPlus | Full Text: PDF(716 KB) **IEEE CNF**

Help Contact Us Privacy &

Indexed by Inspec

© Copyright 2005 IEEE –

	Type	L #	Hits	Search Text	DBs
12	BRS	L12	2182	electromigration and conductor	USPAT; USOCR; EPO; JPO; IBM_TDB
13	BRS	L13	21	12 and plugs and windows	USPAT; USOCR; EPO; JPO; IBM_TDB